

## INFORMATION DISCLOSURE CITATION

ATTY. DOCKET NO.

**SERIAL NO.**

1883-36

### To Be Assigned

APPLICANT

KURAHASHI et al

FILING DATE

**GROUP**

(Use several sheets if necessary)

June 30, 2000


## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)**

<div style="text-align: center;">  </div>	High Brightness Visible (660 nm) Resonant-Cavity Light-Emitting Diode" (IEEE PHOTONICS TECHNOLOGY LETTERS, VOL. 10, No. 12, December 1998)		
*Examiner	Kang, Donglee	Date Considered	6-11-03

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)

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09/607,965

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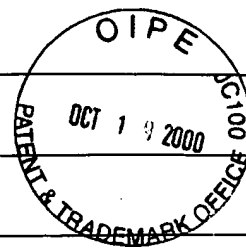
KURAHASHI et al

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2811



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## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

**OTHER DOCUMENTS** (including Author, Title, Date, Pertinent pages, etc.)

DLA	Streubel et al, "High Brightness Visible (660 nm) Resonant-Cavity Light-Emitting Diode", IEEE PHOTONICS TECHNOLOGY LETTERS, Vol. 10, No. 12, December 1998, pages 1685-1687
DLA	USSN 09/645,571, filed August 25, 2000, entitled "SEMICONDUCTOR LIGHT-EMITTING DEVICE AND METHOD FOR FABRICATING THE DEVICE"

\*Examiner

Kang, Donghee

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